



Package Style: QFN, 16-pin, 3mmx3mm

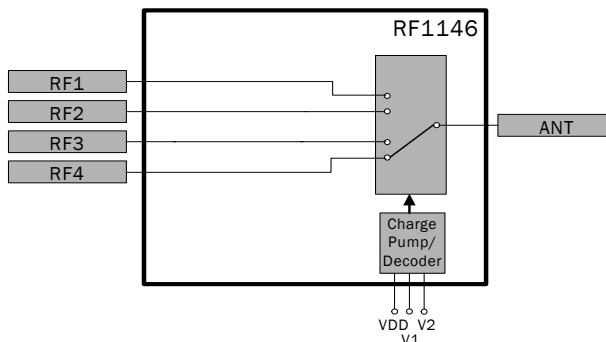


## Features

- Low Frequency - 2.5GHz Operation
- Very Low Insertion Loss:  
Cell Band 0.35dB  
PCS Band 0.45dB
- High Isolation:  
Cell Band 29dB  
PCS Band 22dB
- Compatible With Low Voltage Logic: ( $V_{HIGH} = 1.8V$ )
- Excellent Linearity Performance (IIP2):  
Cell Band 106dBm  
PCS Band 110dBm
- Lowest BOM Cost and Small Solution Size: No DC Blocking Capacitors Required on the RF Paths

## Applications

- Cellular Handset Applications
- Cellular Infrastructure Applications



Functional Block Diagram

## Product Description

The RF1146 is a single-pole four-throw (SP4T) switch designed for general purpose switching applications which require very low insertion loss and low power handling capability.

The RF1146 is ideally suited for battery operated applications requiring high performance switching with very low DC power consumption. The RF1146 features very low insertion loss with excellent linearity performance down to 1.8V control voltage. Additionally, RF1146 includes integrated decoding logic, allowing just two control lines needed for switch control. The RF1146 is packaged in a very compact 3mmx3mmx0.6mm, 16-pin, leadless QFN package. No DC-blocking capacitors are required on RF paths, unless DC is applied externally to the device ports.

## Ordering Information

RF1146	Broadband Low Power SP4T Switch
RF1146PCBA-410	Fully Assembled Evaluation Board

## Optimum Technology Matching® Applied

- |                                      |                                      |  |                                   |
|--------------------------------------|--------------------------------------|--|-----------------------------------|
| <input type="checkbox"/> GaAs HBT    | <input type="checkbox"/> SiGe BiCMOS | <input checked="" type="checkbox"/> GaAs pHEMT | <input type="checkbox"/> GaN HEMT |
| <input type="checkbox"/> GaAs MESFET | <input type="checkbox"/> Si BiCMOS   | <input checked="" type="checkbox"/> Si CMOS    | <input type="checkbox"/> RF MEMS  |
| <input type="checkbox"/> InGaP HBT   | <input type="checkbox"/> SiGe HBT    | <input type="checkbox"/> Si BJT                | <input type="checkbox"/> LDMOS    |

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## Absolute Maximum Ratings

Parameter	Rating	Unit
V <sub>DD</sub> , V1, V2	6.0	V
Maximum Input Power (DC to 2.5GHz, 2.5V Control)	28	dBm
Operating Temperature	-30 to +85	°C
Storage Temperature	-65 to +100	°C



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

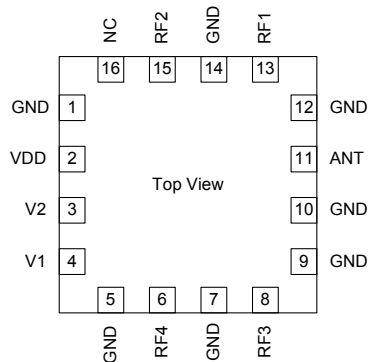
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Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Operating Characteristics					Active Mode: V <sub>HIGH</sub> ≥ 1.8V, V <sub>LOW</sub> ≤ 0.4V; V <sub>DD</sub> = 2.75V; Temp = 25 °C; P <sub>IN</sub> = 26dBm unless otherwise specified.
<b>Insertion Loss</b>					
RF1-ANT, RF2-ANT, RF3-ANT, RF4-ANT		0.35	0.50	dB	824 MHz to 960 MHz
		0.35	0.60	dB	1574 MHz to 1577 MHz
		0.45	0.65	dB	1850 MHz to 1990 MHz
		0.55	0.70		2170 MHz to 2500 MHz
<b>Isolation</b>					
RF1-ANT, RF2-ANT, RF3-ANT, RF4-ANT	18	29		dB	824 MHz to 960 MHz
	22	24		dB	1574 MHz to 1577 MHz
	20	22		dB	1850 MHz to 1990 MHz
	17	20		dB	2170 MHz to 2500 MHz
<b>Return Loss</b>					
RF1-ANT, RF2-ANT, RF3-ANT, RF4-ANT	19			dB	600 MHz to 2500 MHz, All RF ports in Insertion Loss state.
<b>Harmonics</b>					
Second Harmonic (2f <sub>0</sub> )	70	86		dBc	f = 880 MHz, P <sub>IN</sub> = 26 dBm
	70	88		dBc	f = 1880 MHz, P <sub>IN</sub> = 26 dBm
Third Harmonic (3f <sub>0</sub> )	70	81		dBc	f = 880 MHz, P <sub>IN</sub> = 26 dBm
	70	79		dBc	f = 1880 MHz, P <sub>IN</sub> = 26 dBm
<b>IIP2</b>					
RF1-ANT, RF2-ANT, RF3-ANT, RF4-ANT (Cell)	102	106		dBm	Tone 1: 824 MHz @ 16 dBm, Tone 2: 1693 MHz @ -20 dBm, Receive Freq: 869 MHz
RF1-ANT, RF2-ANT, RF3-ANT, RF4-ANT (AWS)	104	108		dBm	Tone 1: 1710 MHz @ 16 dBm, Tone 2: 3820 MHz @ -20 dBm, Receive Freq: 2110 MHz
RF1-ANT, RF2-ANT, RF3-ANT, RF4-ANT (PCS)	106	110		dBm	Tone 1: 1850 MHz @ 16 dBm, Tone 2: 3780 MHz @ -20 dBm, Receive Freq: 1930 MHz
<b>Triple Beat Ration (TBR)</b>					
RF1-ANT, RF2-ANT, RF3-ANT, RF4-ANT (Cell)	65	68		dBc	VSWR = 2:1; Temp = 15 °C, 25 °C, 60 °C; Jammer Freq = 881.5 MHz
RF1-ANT, RF2-ANT, RF3-ANT, RF4-ANT (PCS)	65	68		dBc	VSWR = 2:1; Temp = 15 °C, 25 °C, 60 °C; Jammer Freq = 1960 MHz
<b>0.1dB Compression (P0.1dB)</b>					
	28			dBm	f = 900 MHz
	28			dBm	f = 1800 MHz

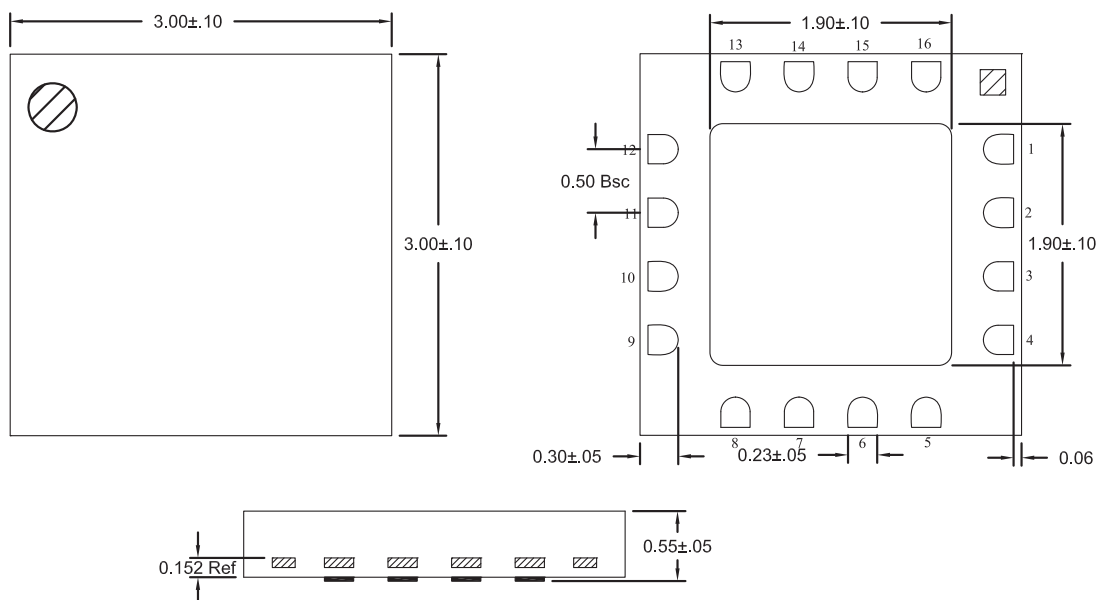
Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
<b>Switching Speed</b>					
		0.55	1.5	us	50% control to 10%/90%
<b>Supply and Control Signal Characteristics</b>					
Switch Supply Voltage ( $V_{DD}$ )	2.50	2.75	3.30	V	Continuously
Supply Current ( $I_{DD}$ )		650	990	$\mu$ A	At Pin = 16 dBm
Control Voltage					
$V_{HIGH}$	1.3	1.8	2.9	V	
$V_{LOW}$	0		0.4	V	
Control Current		0.1	1	$\mu$ A	$P_{IN} = 16$ dBm

Pin	Function	Description
1	GND	Ground
2	VDD	Supply
3	V2	Control Signal 2
4	V1	Control Signal 1
5	GND	Ground
6	RF4	RF Output 4
7	GND	Ground
8	RF3	RF Output 3
9	GND	Ground
10	GND	Ground
11	ANT	RF input. Connected to antenna
12	GND	Ground
13	RF1	RF Output 1
14	GND	Ground
15	RF2	RF Output 2
16	NC	Can be left floating or grounded
PKG BASE	GND	Ground

## Pin Out



## Package Drawing



### NOTES:

1) PIN 1 SHADED AREA

## General Information

### Control Logic

The switch is operable in four states (see Truth table, below). The switch is designed for two modes: Active and Stand-by. These modes are controlled by the  $V_{DD}$  signal. When VDD is high, the switch is active.

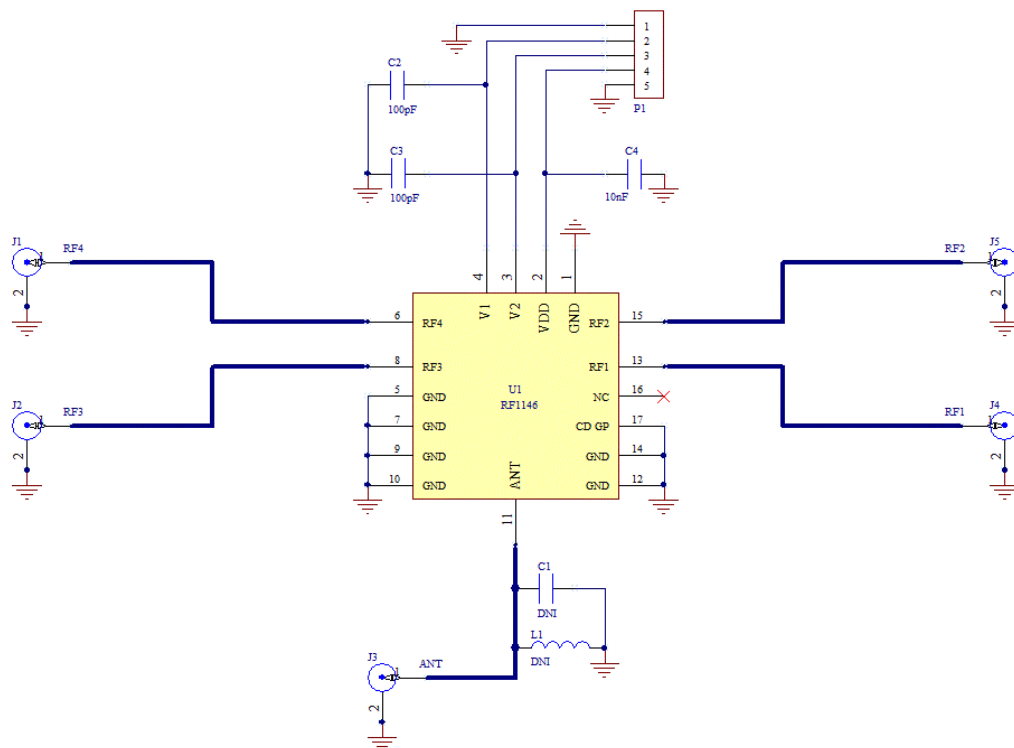
### Control Logic

Mode	V1	V2	S1	S2	S3	S4
ANT-RF1	Low	Low	ON	OFF	OFF	OFF
ANT-RF2	High	Low	OFF	ON	OFF	OFF
ANT-RF3	Low	High	OFF	OFF	ON	OFF
ANT-RF4	High	High	OFF	OFF	OFF	ON

### Electrical Test Methods

The electrical parameters for the switch were measured on test Evaluation Board provided by the switch supplier. The test Evaluation Board includes means for decoupling RF signals from control signal port (shunt capacitor at control signal ports).

All measurements are done with calibration plane at switch pins. The effect of test board losses and phase delay has been removed from the results.



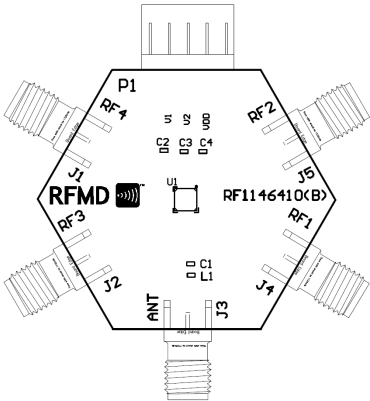
The decoupling capacitors are optional and, if necessary, may be used for noise reduction. Decoupling capacitors on the control pins protect the control circuitry from possible RF leakage. DC Blocking capacitors are not needed on the RF paths as there is no DC on the RF paths, however care should be taken to ensure that DC is not injected into the switch from external circuitry. An ESD filter is needed to protect the switch from antenna ESD events. The filter is formed by LESD inductor and CESD capacitor. The switch has a supply input to feed the built-in logic decoding.

\*LESD value will depend on the level of ESD protection and the loss acceptable in a given application.

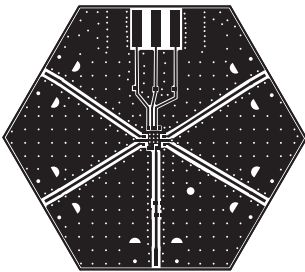
## Evaluation Board Layout

Board Thickness 0.0658", Board Material FR-4

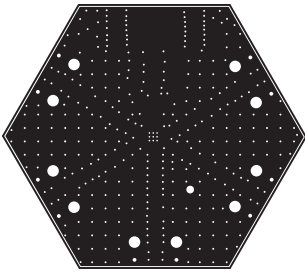
Component Layer



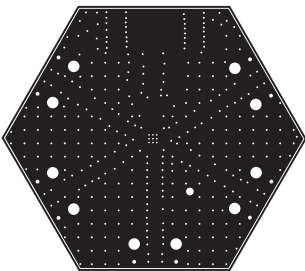
Topside RF Layer



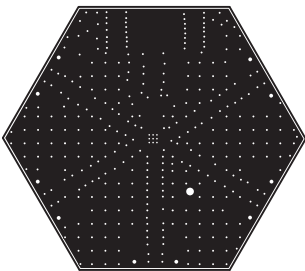
Inner Layer 1



Inner Layer 2



Ground Plane Layer



Typical Performance Data on Evaluation Board



Fixture losses have been de-embedded (Temp=25 °C,  $V_{DD}$ =2.75V,  $V_{CONTROL}$  High=1.8V,  $V_{CONTROL}$  Low=0V)

